

## TRIPLE-CHANNEL DIGITAL ISOLATOR

### Features

- High-speed operation:  
DC – 150 Mbps
- Low propagation delay:  
<10 ns
- Wide Operating Supply Voltage:  
2.375-5.5V
- Low power:  $I_1 + I_2 < 12$  mA/channel at 100 Mbps
- Precise timing:  
2 ns pulse width distortion  
1 ns channel-channel matching  
2 ns pulse width skew
- 2500 V<sub>RMS</sub> isolation
- Transient Immunity: >25 kV/μs
- Tri-state outputs with ENABLE control
- DC correct
- No start-up initialization required
- <10 μs Startup Time
- High temperature operation:  
125 °C at 100 Mbps  
100 °C at 150 Mbps
- Wide body SOIC-16 package

### Applications

- Isolated switch mode supplies
- Isolated ADC, DAC
- Motor control
- Power factor correction systems

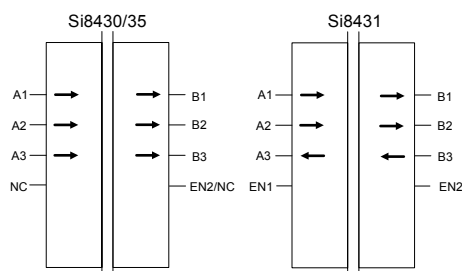
### Safety Regulatory Approvals

- UL recognition: 2500 V<sub>RMS</sub> for 1 Minute per UL1577
- CSA component acceptance notice
- VDE certification conformity
  - IEC 60747-5-2 (VDE0884 Part 2)

### Description

Silicon Lab's family of digital isolators are CMOS devices that employ an RF coupler to transmit digital information across an isolation barrier. Very high speed operation at low power levels is achieved. These parts are available in a 16-pin wide body SOIC package. Three speed grade options (1, 10, 150 Mbps) are available and achieve typical propagation delay of less than 10 ns.

### Block Diagram



### Pin Assignments

#### Wide Body SOIC

|                  |   |    |                  |
|------------------|---|----|------------------|
| V <sub>DD1</sub> | 1 | 16 | V <sub>DD2</sub> |
| GND1             | 2 | 15 | GND2             |
| A1               | 3 | 14 | B1               |
| A2               | 4 | 13 | B2               |
| A3               | 5 | 12 | B3               |
| NC               | 6 | 11 | NC               |
| EN1/NC           | 7 | 10 | EN2/NC           |
| GND1             | 8 | 9  | GND2             |

Top View

# Si8430/31/35

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## 1. Electrical Specifications

**Table 1. Electrical Characteristics**

( $V_{DD1} = 5\text{ V}$ ,  $V_{DD2} = 5\text{ V}$ ,  $T_A = -40\text{ to }125\text{ }^{\circ}\text{C}$ )

| Parameter                                                                                                        | Symbol    | Test Condition          | Min                      | Typ | Max      | Unit          |
|------------------------------------------------------------------------------------------------------------------|-----------|-------------------------|--------------------------|-----|----------|---------------|
| High Level Input Voltage                                                                                         | $V_{IH}$  |                         | 2.0                      | —   | —        | V             |
| Low Level Input Voltage                                                                                          | $V_{IL}$  |                         | —                        | —   | 0.8      | V             |
| High Level Output Voltage                                                                                        | $V_{OH}$  | $I_{OH} = -4\text{ mA}$ | $V_{DD1}, V_{DD2} - 0.4$ | 4.8 | —        | V             |
| Low Level Output Voltage                                                                                         | $V_{OL}$  | $I_{OL} = 4\text{ mA}$  | —                        | 0.2 | 0.4      | V             |
| Input Leakage Current                                                                                            | $I_L$     |                         | —                        | —   | $\pm 10$ | $\mu\text{A}$ |
| Enable Input High Current                                                                                        | $I_{ENH}$ | $V_{ENx} = V_{IH}$      | —                        | 4   | —        | $\mu\text{A}$ |
| Enable Input Low Current                                                                                         | $I_{ENL}$ | $V_{ENx} = V_{IL}$      | —                        | 20  | —        | $\mu\text{A}$ |
| <b>DC Supply Current (All inputs 0 V or at Supply)</b>                                                           |           |                         |                          |     |          |               |
| Si8430/35-A,-B,-C, $V_{DD1}$                                                                                     |           | All inputs 0 DC         | —                        | 7   | 10       | mA            |
| Si8430/35-A,-B,-C, $V_{DD2}$                                                                                     |           | All inputs 0 DC         | —                        | 6   | 9        | mA            |
| Si8430/35-A,-B,-C, $V_{DD1}$                                                                                     |           | All inputs 1 DC         | —                        | 14  | 18       | mA            |
| Si8430/35-A,-B,-C, $V_{DD2}$                                                                                     |           | All inputs 1 DC         | —                        | 6   | 9        | mA            |
| Si8431-A,-B,-C, $V_{DD1}$                                                                                        |           | All inputs 0 DC         | —                        | 8   | 12       | mA            |
| Si8431-A,-B,-C, $V_{DD2}$                                                                                        |           | All inputs 0 DC         | —                        | 10  | 15       | mA            |
| Si8431-A,-B,-C, $V_{DD1}$                                                                                        |           | All inputs 1 DC         | —                        | 13  | 19       | mA            |
| Si8431-A,-B,-C, $V_{DD2}$                                                                                        |           | All inputs 1 DC         | —                        | 12  | 17       | mA            |
| <b>10 Mbps Supply Current (All inputs = 5 MHz square wave, <math>C_I = 15\text{ pF}</math> on all outputs)</b>   |           |                         |                          |     |          |               |
| Si8430/35-B,-C, $V_{DD1}$                                                                                        |           |                         | —                        | 11  | 15       | mA            |
| Si8430/35-B,-C, $V_{DD2}$                                                                                        |           |                         | —                        | 13  | 17       | mA            |
| Si8431-B,-C, $V_{DD1}$                                                                                           |           |                         | —                        | 12  | 16       | mA            |
| Si8431-B,-C, $V_{DD2}$                                                                                           |           |                         | —                        | 13  | 17       | mA            |
| <b>100 Mbps Supply Current (All inputs = 50 MHz square wave, <math>C_I = 15\text{ pF}</math> on all outputs)</b> |           |                         |                          |     |          |               |
| Si8430-C, $V_{DD1}$                                                                                              |           |                         | —                        | 11  | 15       | mA            |
| Si8430-C, $V_{DD2}$                                                                                              |           |                         | —                        | 23  | 28       | mA            |
| Si8431-C, $V_{DD1}$                                                                                              |           |                         | —                        | 13  | 18       | mA            |
| Si8431-C, $V_{DD2}$                                                                                              |           |                         | —                        | 21  | 26       | mA            |

[查询"SI8430"供应商](#)**Table 1. Electrical Characteristics (Continued)**(V<sub>DD1</sub> = 5 V, V<sub>DD2</sub> = 5 V, T<sub>A</sub> = -40 to 125 °C)

| Parameter                                                      | Symbol                              | Test Condition | Min | Typ | Max  | Unit |
|----------------------------------------------------------------|-------------------------------------|----------------|-----|-----|------|------|
| <b>Timing Characteristics</b>                                  |                                     |                |     |     |      |      |
| <b>Si843x-A</b>                                                |                                     |                |     |     |      |      |
| Maximum Data Rate                                              |                                     |                | 0   | —   | 1    | Mbps |
| Minimum Pulse Width                                            |                                     |                | —   | —   | 1000 | ns   |
| Propagation Delay                                              | t <sub>PHL</sub> , t <sub>PLH</sub> | See Figure 2   | —   | —   | 75   | ns   |
| Pulse Width Distortion<br> t <sub>PLH</sub> - t <sub>PHL</sub> | PWD                                 | See Figure 2   | —   | —   | 30   | ns   |
| Propagation Delay Skew <sup>1</sup>                            | t <sub>PSK(P-P)</sub>               |                | —   | —   | 50   | ns   |
| Channel-Channel Skew                                           | t <sub>PSK</sub>                    |                | —   | —   | 40   | ns   |
| <b>Si843x-B</b>                                                |                                     |                |     |     |      |      |
| Maximum Data Rate                                              |                                     |                | 0   | —   | 10   | Mbps |
| Minimum Pulse Width                                            |                                     |                | —   | —   | 100  | ns   |
| Propagation Delay                                              | t <sub>PHL</sub> , t <sub>PLH</sub> | See Figure 2   | —   | —   | 35   | ns   |
| Pulse Width Distortion<br> t <sub>PLH</sub> - t <sub>PHL</sub> | PWD                                 | See Figure 2   | —   | —   | 7.5  | ns   |
| Propagation Delay Skew <sup>1</sup>                            | t <sub>PSK(P-P)</sub>               |                | —   | —   | 25   | ns   |
| Channel-Channel Skew                                           | t <sub>PSK</sub>                    |                | —   | —   | 5    | ns   |
| <b>Si843x-C</b>                                                |                                     |                |     |     |      |      |
| Maximum Data Rate                                              |                                     |                | 0   | —   | 150  | Mbps |
| Minimum Pulse Width                                            |                                     |                | —   | —   | 6.6  | ns   |
| Propagation Delay                                              | t <sub>PHL</sub> , t <sub>PLH</sub> | See Figure 2   | 4   | 6.5 | 9.5  | ns   |
| Pulse Width Distortion<br> t <sub>PLH</sub> - t <sub>PHL</sub> | PWD                                 | See Figure 2   | —   | —   | 3    | ns   |
| Propagation Delay Skew <sup>1</sup>                            | t <sub>PSK(P-P)</sub>               |                | —   | —   | 5.5  | ns   |
| Channel-Channel Skew                                           | t <sub>PSK</sub>                    |                | —   | —   | 3    | ns   |

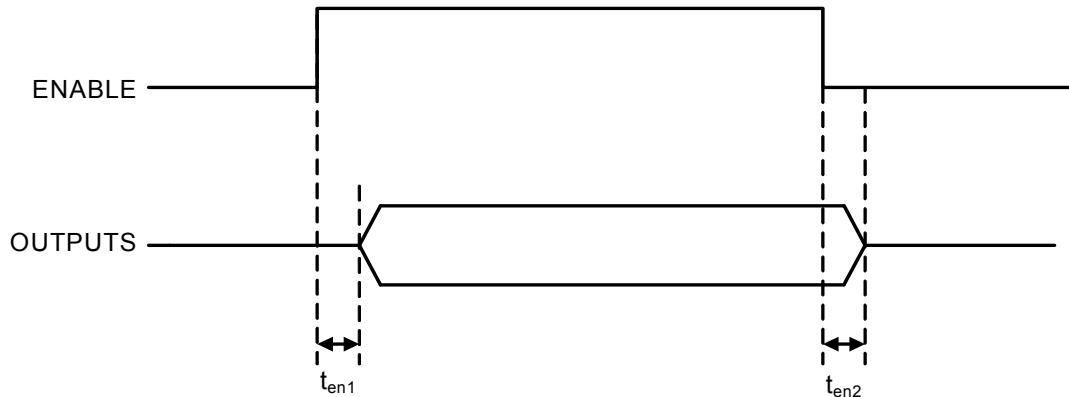
**Table 1. Electrical Characteristics (Continued)**

( $V_{DD1} = 5\text{ V}$ ,  $V_{DD2} = 5\text{ V}$ ,  $T_A = -40\text{ to }125\text{ }^{\circ}\text{C}$ )

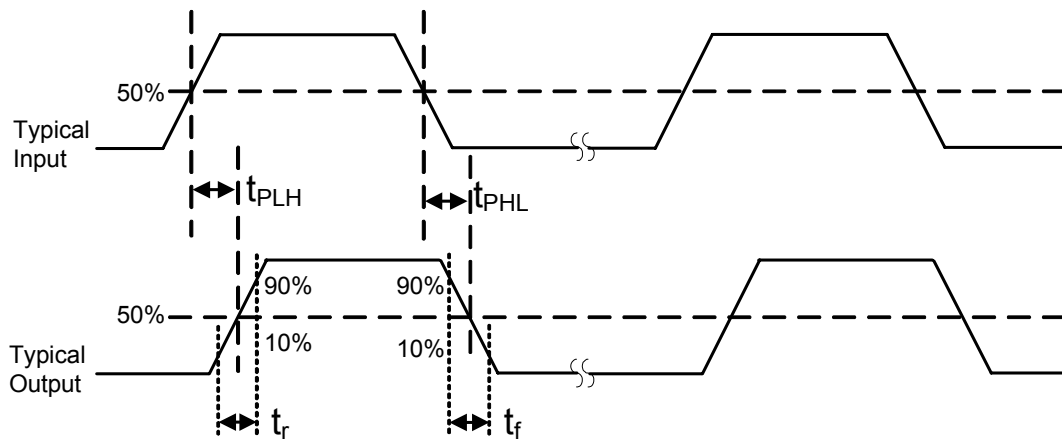
| Parameter                      | Symbol    | Test Condition                       | Min | Typ | Max | Unit              |
|--------------------------------|-----------|--------------------------------------|-----|-----|-----|-------------------|
| <b>For All Models</b>          |           |                                      |     |     |     |                   |
| Output Rise Time               | $t_r$     | $C_L = 15\text{ pF}$<br>See Figure 2 | —   | 2   | —   | ns                |
| Output Fall Time               | $t_f$     | $C_L = 15\text{ pF}$<br>See Figure 2 | —   | 2   | —   | ns                |
| Common Mode Transient Immunity | CTMI      | $V_I = V_{DD}$ or $0\text{ V}$       | 25  | 30  | —   | kV/ $\mu\text{s}$ |
| Enable to Data Valid           | $t_{en1}$ | See Figure 1                         | —   | 5   | —   | ns                |
| Enable to Data Tri-State       | $t_{en2}$ | See Figure 1                         | —   | 5   | —   | ns                |
| Start-up Time <sup>2</sup>     | $t_{SU}$  |                                      | —   | 3   | —   | $\mu\text{s}$     |

**Notes:**

1.  $t_{PSK(P-P)}$  is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature.
2. Start-up time is the time period from the application of power to valid data at the output.



**Figure 1. ENABLE Timing Diagram**



**Figure 2. Propagation Delay Timing**

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**Table 2. Electrical Characteristics**(V<sub>DD1</sub> = 3.3 V, V<sub>DD2</sub> = 3.3 V, T<sub>A</sub> = -40 to 125 °C)

| Parameter                                                                                   | Symbol           | Test Condition                     | Min                                       | Typ | Max | Unit |
|---------------------------------------------------------------------------------------------|------------------|------------------------------------|-------------------------------------------|-----|-----|------|
| High Level Input Voltage                                                                    | V <sub>IH</sub>  |                                    | 2.0                                       | —   | —   | V    |
| Low Level Input Voltage                                                                     | V <sub>IL</sub>  |                                    | —                                         | —   | 0.8 | V    |
| High Level Output Voltage                                                                   | V <sub>OH</sub>  | I <sub>oh</sub> = -4 mA            | V <sub>DD1</sub> , V <sub>DD2</sub> - 0.4 | 3.1 | —   | V    |
| Low Level Output Voltage                                                                    | V <sub>OL</sub>  | I <sub>ol</sub> = 4 mA             | —                                         | 0.2 | 0.4 | V    |
| Input Leakage Current                                                                       | I <sub>L</sub>   |                                    | —                                         | —   | ±10 | μA   |
| Enable Input High Current                                                                   | I <sub>ENH</sub> | V <sub>ENx</sub> = V <sub>IH</sub> | —                                         | 4   | —   | μA   |
| Enable Input Low Current                                                                    | I <sub>ENL</sub> | V <sub>ENx</sub> = V <sub>IL</sub> | —                                         | 20  | —   | μA   |
| <b>DC Supply Current (All inputs 0 V or at supply)</b>                                      |                  |                                    |                                           |     |     |      |
| Si8430/35-A,-B,-C, V <sub>DD1</sub>                                                         |                  | All inputs 0 DC                    | —                                         | 7   | 10  | mA   |
| Si8430/35-A,-B,-C, V <sub>DD2</sub>                                                         |                  | All inputs 0 DC                    | —                                         | 6   | 9   | mA   |
| Si8430/35-A,-B,-C, V <sub>DD1</sub>                                                         |                  | All inputs 1 DC                    | —                                         | 13  | 17  | mA   |
| Si8430/35-A,-B,-C, V <sub>DD2</sub>                                                         |                  | All inputs 1 DC                    | —                                         | 5   | 8   | mA   |
| Si8431-A,-B,-C, V <sub>DD1</sub>                                                            |                  | All inputs 0 DC                    | —                                         | 7   | 11  | mA   |
| Si8431-A,-B,-C, V <sub>DD2</sub>                                                            |                  | All inputs 0 DC                    | —                                         | 10  | 15  | mA   |
| Si8431-A,-B,-C, V <sub>DD1</sub>                                                            |                  | All inputs 1 DC                    | —                                         | 12  | 18  | mA   |
| Si8431-A,-B,-C, V <sub>DD2</sub>                                                            |                  | All inputs 1 DC                    | —                                         | 11  | 16  | mA   |
| <b>10 Mbps Supply Current (All inputs = 5 MHz square wave, CI = 15 pF on all outputs)</b>   |                  |                                    |                                           |     |     |      |
| Si8430/35-B,-C, V <sub>DD1</sub>                                                            |                  |                                    | —                                         | 10  | 14  | mA   |
| Si8430/35-B,-C, V <sub>DD2</sub>                                                            |                  |                                    | —                                         | 11  | 16  | mA   |
| Si8431-B,-C, V <sub>DD1</sub>                                                               |                  |                                    | —                                         | 10  | 15  | mA   |
| Si8431-B,-C, V <sub>DD2</sub>                                                               |                  |                                    | —                                         | 13  | 18  | mA   |
| <b>100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)</b> |                  |                                    |                                           |     |     |      |
| Si8430-C, V <sub>DD1</sub>                                                                  |                  |                                    | —                                         | 11  | 15  | mA   |
| Si8430-C, V <sub>DD2</sub>                                                                  |                  |                                    | —                                         | 16  | 20  | mA   |
| Si8431-C, V <sub>DD1</sub>                                                                  |                  |                                    | —                                         | 12  | 18  | mA   |
| Si8431-C, V <sub>DD2</sub>                                                                  |                  |                                    | —                                         | 19  | 25  | mA   |

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**Table 2. Electrical Characteristics (Continued)**

( $V_{DD1} = 3.3\text{ V}$ ,  $V_{DD2} = 3.3\text{ V}$ ,  $T_A = -40\text{ to }125\text{ }^{\circ}\text{C}$ )

| Parameter                                       | Symbol                | Test Condition | Min | Typ | Max  | Unit |
|-------------------------------------------------|-----------------------|----------------|-----|-----|------|------|
| <b>Timing Characteristics</b>                   |                       |                |     |     |      |      |
| <b>Si843x-A</b>                                 |                       |                |     |     |      |      |
| Maximum Data Rate                               |                       |                | 0   | —   | 1    | Mbps |
| Minimum Pulse Width                             |                       |                | —   | —   | 1000 | ns   |
| Propagation Delay                               | $t_{PHL}$ , $t_{PLH}$ | See Figure 2   | —   | —   | 75   | ns   |
| Pulse Width Distortion<br>$ t_{PLH} - t_{PHL} $ | PWD                   | See Figure 2   | —   | —   | 30   | ns   |
| Propagation Delay Skew <sup>1</sup>             | $t_{PSK(P-P)}$        |                | —   | —   | 50   | ns   |
| Channel-Channel Skew                            | $t_{PSK}$             |                | —   | —   | 40   | ns   |
| <b>Si843x-B</b>                                 |                       |                |     |     |      |      |
| Maximum Data Rate                               |                       |                | 0   | —   | 10   | Mbps |
| Minimum Pulse Width                             |                       |                | —   | —   | 100  | ns   |
| Propagation Delay                               | $t_{PHL}$ , $t_{PLH}$ | See Figure 2   | —   | —   | 35   | ns   |
| Pulse Width Distortion<br>$ t_{PLH} - t_{PHL} $ | PWD                   | See Figure 2   | —   | —   | 7.5  | ns   |
| Propagation Delay Skew <sup>1</sup>             | $t_{PSK(P-P)}$        |                | —   | —   | 25   | ns   |
| Channel-Channel Skew                            | $t_{PSK}$             |                | —   | —   | 5    | ns   |
| <b>Si843x-C</b>                                 |                       |                |     |     |      |      |
| Maximum Data Rate                               |                       |                | 0   | —   | 150  | Mbps |
| Minimum Pulse Width                             |                       |                | —   | —   | 6.6  | ns   |
| Propagation Delay                               | $t_{PHL}$ , $t_{PLH}$ | See Figure 2   | 4   | 6.5 | 9.5  | ns   |
| Pulse Width Distortion<br>$ t_{PLH} - t_{PHL} $ | PWD                   | See Figure 2   | —   | —   | 3    | ns   |
| Propagation Delay Skew <sup>1</sup>             | $t_{PSK(P-P)}$        |                | —   | —   | 5.5  | ns   |
| Channel-Channel Skew                            | $t_{PSK}$             |                | —   | —   | 3    | ns   |



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**Table 2. Electrical Characteristics (Continued)**(V<sub>DD1</sub> = 3.3 V, V<sub>DD2</sub> = 3.3 V, T<sub>A</sub> = -40 to 125 °C)

| Parameter                      | Symbol           | Test Condition                          | Min | Typ | Max | Unit  |
|--------------------------------|------------------|-----------------------------------------|-----|-----|-----|-------|
| <b>For All Models</b>          |                  |                                         |     |     |     |       |
| Output Rise Time               | t <sub>r</sub>   | C <sub>L</sub> = 15 pF<br>See Figure 2  | —   | 2   | —   | ns    |
| Output Fall Time               | t <sub>f</sub>   | C <sub>L</sub> = 15 pF<br>See Figure 2  | —   | 2   | —   | ns    |
| Common Mode Transient Immunity | CTMI             | V <sub>I</sub> = V <sub>DD</sub> or 0 V | 25  | 30  | —   | kV/μs |
| Enable to Data Valid           | t <sub>en1</sub> | See Figure 1                            | —   | 5   | —   | ns    |
| Enable to Data Tri-State       | t <sub>en2</sub> | See Figure 1                            | —   | 5   | —   | ns    |
| Start-up Time <sup>2</sup>     | t <sub>su</sub>  |                                         | —   | 3   | —   | μs    |

**Notes:**

1. t<sub>PSK(P-P)</sub> is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature.
2. Start-up time is the time period from the application of power to valid data at the output.

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**Table 3. Electrical Characteristics**

( $V_{DD1} = 2.5\text{ V}$ ,  $V_{DD2} = 2.5\text{ V}$ ,  $T_A = -40\text{ to }100\text{ }^{\circ}\text{C}$ )

| Parameter                                                                                                        | Symbol    | Test Condition          | Min                      | Typ | Max      | Unit          |
|------------------------------------------------------------------------------------------------------------------|-----------|-------------------------|--------------------------|-----|----------|---------------|
| High Level Input Voltage                                                                                         | $V_{IH}$  |                         | 2.0                      | —   | —        | V             |
| Low Level Input Voltage                                                                                          | $V_{IL}$  |                         | —                        | —   | 0.8      | V             |
| High Level Output Voltage                                                                                        | $V_{OH}$  | $I_{OH} = -4\text{ mA}$ | $V_{DD1}, V_{DD2} - 0.4$ | 2.3 | —        | V             |
| Low Level Output Voltage                                                                                         | $V_{OL}$  | $I_{OL} = 4\text{ mA}$  | —                        | 0.2 | 0.4      | V             |
| Input Leakage Current                                                                                            | $I_L$     |                         | —                        | —   | $\pm 10$ | $\mu\text{A}$ |
| Enable Input High Current                                                                                        | $I_{ENH}$ | $V_{ENx} = V_{IH}$      | —                        | 4   | —        | $\mu\text{A}$ |
| Enable Input Low Current                                                                                         | $I_{ENL}$ | $V_{ENx} = V_{IL}$      | —                        | 20  | —        | $\mu\text{A}$ |
| <b>DC Supply Current (All inputs 0 V or at supply)</b>                                                           |           |                         |                          |     |          |               |
| Si8430/35-A,-B,-C, $V_{DD1}$                                                                                     |           | All inputs 0 DC         | —                        | 6   | 8        | mA            |
| Si8430/35-A,-B,-C, $V_{DD2}$                                                                                     |           | All inputs 0 DC         | —                        | 5   | 7        | mA            |
| Si8430/35-A,-B,-C, $V_{DD1}$                                                                                     |           | All inputs 1 DC         | —                        | 11  | 13       | mA            |
| Si8430/35-A,-B,-C, $V_{DD2}$                                                                                     |           | All inputs 1 DC         | —                        | 5   | 7        | mA            |
| Si8431-A,-B,-C, $V_{DD1}$                                                                                        |           | All inputs 0 DC         | —                        | 7   | 10       | mA            |
| Si8431-A,-B,-C, $V_{DD2}$                                                                                        |           | All inputs 0 DC         | —                        | 9   | 11       | mA            |
| Si8431-A,-B,-C, $V_{DD1}$                                                                                        |           | All inputs 1 DC         | —                        | 11  | 13       | mA            |
| Si8431-A,-B,-C, $V_{DD2}$                                                                                        |           | All inputs 1 DC         | —                        | 9   | 11       | mA            |
| <b>10 Mbps Supply Current (All inputs = 5 MHz square wave, <math>C_I = 15\text{ pF}</math> on all outputs)</b>   |           |                         |                          |     |          |               |
| Si8430/35-B,-C, $V_{DD1}$                                                                                        |           |                         | —                        | 9   | 11       | mA            |
| Si8430/35-B,-C, $V_{DD2}$                                                                                        |           |                         | —                        | 8   | 10       | mA            |
| Si8431-B,-C, $V_{DD1}$                                                                                           |           |                         | —                        | 9   | 11       | mA            |
| Si8431-B,-C, $V_{DD2}$                                                                                           |           |                         | —                        | 10  | 13       | mA            |
| <b>100 Mbps Supply Current (All inputs = 50 MHz square wave, <math>C_I = 15\text{ pF}</math> on all outputs)</b> |           |                         |                          |     |          |               |
| Si8430-C, $V_{DD1}$                                                                                              |           |                         | —                        | 10  | 12       | mA            |
| Si8430-C, $V_{DD2}$                                                                                              |           |                         | —                        | 12  | 15       | mA            |
| Si8431-C, $V_{DD1}$                                                                                              |           |                         | —                        | 12  | 15       | mA            |
| Si8431-C, $V_{DD2}$                                                                                              |           |                         | —                        | 15  | 19       | mA            |

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**Table 3. Electrical Characteristics (Continued)**(V<sub>DD1</sub> = 2.5 V, V<sub>DD2</sub> = 2.5 V, T<sub>A</sub> = -40 to 100 °C)

| Parameter                                                      | Symbol                              | Test Condition | Min | Typ | Max  | Unit |
|----------------------------------------------------------------|-------------------------------------|----------------|-----|-----|------|------|
| <b>Timing Characteristics</b>                                  |                                     |                |     |     |      |      |
| <b>Si843x-A</b>                                                |                                     |                |     |     |      |      |
| Maximum Data Rate                                              |                                     |                | 0   | —   | 1    | Mbps |
| Minimum Pulse Width                                            |                                     |                | —   | —   | 1000 | ns   |
| Propagation Delay                                              | t <sub>PHL</sub> , t <sub>PLH</sub> | See Figure 2   | —   | —   | 75   | ns   |
| Pulse Width Distortion<br> t <sub>PLH</sub> - t <sub>PHL</sub> | PWD                                 | See Figure 2   | —   | —   | 30   | ns   |
| Propagation Delay Skew <sup>1</sup>                            | t <sub>PSK(P-P)</sub>               |                | —   | —   | 50   | ns   |
| Channel-Channel Skew                                           | t <sub>PSK</sub>                    |                | —   | —   | 40   | ns   |
| <b>Si843x-B</b>                                                |                                     |                |     |     |      |      |
| Maximum Data Rate                                              |                                     |                | 0   | —   | 10   | Mbps |
| Minimum Pulse Width                                            |                                     |                | —   | —   | 100  | ns   |
| Propagation Delay                                              | t <sub>PHL</sub> , t <sub>PLH</sub> | See Figure 2   | —   | —   | 35   | ns   |
| Pulse Width Distortion<br> t <sub>PLH</sub> - t <sub>PHL</sub> | PWD                                 | See Figure 2   | —   | —   | 7.5  | ns   |
| Propagation Delay Skew <sup>1</sup>                            | t <sub>PSK(P-P)</sub>               |                | —   | —   | 25   | ns   |
| Channel-Channel Skew                                           | t <sub>PSK</sub>                    |                | —   | —   | 5    | ns   |
| <b>Si843x-C</b>                                                |                                     |                |     |     |      |      |
| Maximum Data Rate                                              |                                     |                | 0   | —   | 100  | Mbps |
| Minimum Pulse Width                                            |                                     |                | —   | —   | 10   | ns   |
| Propagation Delay                                              | t <sub>PHL</sub> , t <sub>PLH</sub> | See Figure 2   | 5   | 10  | 17   | ns   |
| Pulse Width Distortion<br> t <sub>PLH</sub> - t <sub>PHL</sub> | PWD                                 | See Figure 2   | —   | —   | 7    | ns   |
| Propagation Delay Skew <sup>1</sup>                            | t <sub>PSK(P-P)</sub>               |                | —   | —   | 12   | ns   |
| Channel-Channel Skew                                           | t <sub>PSK</sub>                    |                | —   | —   | 4    | ns   |

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**Table 3. Electrical Characteristics (Continued)**

( $V_{DD1} = 2.5\text{ V}$ ,  $V_{DD2} = 2.5\text{ V}$ ,  $T_A = -40\text{ to }100\text{ }^{\circ}\text{C}$ )

| Parameter                                                                                                                                                                              | Symbol    | Test Condition                       | Min | Typ | Max | Unit              |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------|--------------------------------------|-----|-----|-----|-------------------|
| <b>For All Models</b>                                                                                                                                                                  |           |                                      |     |     |     |                   |
| Output Rise Time                                                                                                                                                                       | $t_r$     | $C_L = 15\text{ pF}$<br>See Figure 2 | —   | 2   | —   | ns                |
| Output Fall Time                                                                                                                                                                       | $t_f$     | $C_L = 15\text{ pF}$<br>See Figure 2 | —   | 2   | —   | ns                |
| Common Mode Transient Immunity                                                                                                                                                         | CTMI      | $V_I = V_{DD}$ or $0\text{ V}$       | 25  | 30  | —   | kV/ $\mu\text{s}$ |
| Enable to Data Valid                                                                                                                                                                   | $t_{en1}$ | See Figure 1                         | —   | 5   | —   | ns                |
| Enable to Data Tri-State                                                                                                                                                               | $t_{en2}$ | See Figure 1                         | —   | 5   | —   | ns                |
| Start-up Time <sup>2</sup>                                                                                                                                                             | $t_{SU}$  |                                      | —   | 3   | —   | $\mu\text{s}$     |
| <b>Notes:</b>                                                                                                                                                                          |           |                                      |     |     |     |                   |
| 1. $t_{PSK(P-P)}$ is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature. |           |                                      |     |     |     |                   |
| 2. Start-up time is the time period from the application of power to valid data at the output.                                                                                         |           |                                      |     |     |     |                   |

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**Table 4. Absolute Maximum Ratings**

| Parameter                                                                                                                                                                                                               | Symbol             | Min  | Typ | Max            | Unit     |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------|------|-----|----------------|----------|
| Storage Temperature                                                                                                                                                                                                     | $T_{STG}$          | -65  | —   | 150            | °C       |
| Operating Temperature                                                                                                                                                                                                   | $T_A$              | -40  | —   | 125            | °C       |
| Supply Voltage                                                                                                                                                                                                          | $V_{DD1}, V_{DD2}$ | -0.5 | —   | 6              | V        |
| Input Voltage                                                                                                                                                                                                           | $V_I$              | -0.5 | —   | $V_{DD} + 0.5$ | V        |
| Output Voltage                                                                                                                                                                                                          | $V_O$              | -0.5 | —   | $V_{DD} + 0.5$ | V        |
| Output Current Drive Channel                                                                                                                                                                                            | $I_O$              | —    | —   | 10             | mA       |
| Lead Solder Temperature (10s)                                                                                                                                                                                           |                    | —    | —   | 260            | °C       |
| Maximum Isolation Voltage                                                                                                                                                                                               |                    | —    | —   | 4000           | $V_{DC}$ |
| <b>Note:</b> Permanent device damage may occur if the above Absolute Maximum Ratings are exceeded. Functional operation should be restricted to conditions as specified in the operational sections of this data sheet. |                    |      |     |                |          |

**Table 5. Recommended Operating Conditions**

| Parameter                                                                                                                                       | Symbol    | Test Condition       | Min   | Typ | Max | Unit |
|-------------------------------------------------------------------------------------------------------------------------------------------------|-----------|----------------------|-------|-----|-----|------|
| Ambient Operating Temperature*                                                                                                                  | $T_A$     | 100 Mbps, 15 pF, 5 V | -40   | 25  | 125 | °C   |
|                                                                                                                                                 |           | 150 Mbps, 15 pF, 5 V | 0     | 25  | 100 | °C   |
| Supply Voltage                                                                                                                                  | $V_{DD1}$ |                      | 2.375 | —   | 5.5 | V    |
|                                                                                                                                                 | $V_{DD2}$ |                      | 2.375 | —   | 5.5 | V    |
| <b>*Note:</b> The maximum ambient temperature is dependent on data frequency, output loading, number of operating channels, and supply voltage. |           |                      |       |     |     |      |

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**Table 6. Regulatory Information**

|                                                                                                                                                                                                                                            |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| <b>CSA</b>                                                                                                                                                                                                                                 |
| The Si84xx is certified under CSA Component Acceptance Notice. For more details, see File 232873.                                                                                                                                          |
| <b>VDE</b>                                                                                                                                                                                                                                 |
| The Si84xx is certified according to IEC 60747-5-2. For more details, see File 5006301-4880-0001.                                                                                                                                          |
| <b>UL</b>                                                                                                                                                                                                                                  |
| The Si84xx is certified under UL1577 component recognition program to provide basic insulation to 2500 V <sub>RMS</sub> (1 minute). It is production tested $\geq 3000$ V <sub>RMS</sub> for 1 second. For more details, see File E257455. |

**Table 7. Insulation and Safety-related Specifications**

| Parameter                                                                                                                                                                                                                                                                                                                                      | Symbol          | Test Condition                | Value            | Unit |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------|-------------------------------|------------------|------|
| Minimum Air Gap (Clearance)                                                                                                                                                                                                                                                                                                                    | L(IO1)          |                               | 7.7 min          | mm   |
| Minimum External Tracking (Creepage)                                                                                                                                                                                                                                                                                                           | L(IO2)          |                               | 8.1              | mm   |
| Minimum Internal Gap (Internal Clearance)                                                                                                                                                                                                                                                                                                      |                 |                               | 0.008 min        | mm   |
| Tracking Resistance (Comparative Tracking Index)                                                                                                                                                                                                                                                                                               | CTI             | DIN IEC 60112/VDE 0303 Part 1 | >175             | V    |
| Resistance (Input-Output) <sup>1</sup>                                                                                                                                                                                                                                                                                                         | R <sub>IO</sub> |                               | 10 <sup>12</sup> | Ω    |
| Capacitance (Input-Output) <sup>1</sup>                                                                                                                                                                                                                                                                                                        | C <sub>IO</sub> | f = 1 MHz                     | 1.4              | pF   |
| Input Capacitance <sup>2</sup>                                                                                                                                                                                                                                                                                                                 | C <sub>I</sub>  |                               | 4.0              | pF   |
| <b>Notes:</b><br>1. To determine resistance and capacitance, the Si84xx is converted into a 2-terminal device. Pins 1–8 are shorted together to form the first terminal and pins 9–16 are shorted together to form the second terminal. The parameters are then measured between these two terminals.<br>2. Measured from input pin to ground. |                 |                               |                  |      |

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Table 8. IEC 60664-1 (VDE 0884 Part 2) Ratings

| Parameter                   | Test Conditions                         | Specification |
|-----------------------------|-----------------------------------------|---------------|
| Basic isolation group       | Material Group                          | IIIa          |
| Installation Classification | Rated Mains Voltages $\leq 150 V_{RMS}$ | I-IV          |
|                             | Rated Mains Voltages $\leq 300 V_{RMS}$ | I-III         |
|                             | Rated Mains Voltages $\leq 400 V_{RMS}$ | I-II          |

Table 9. IEC 60747-5-2 Insulation Characteristics\*

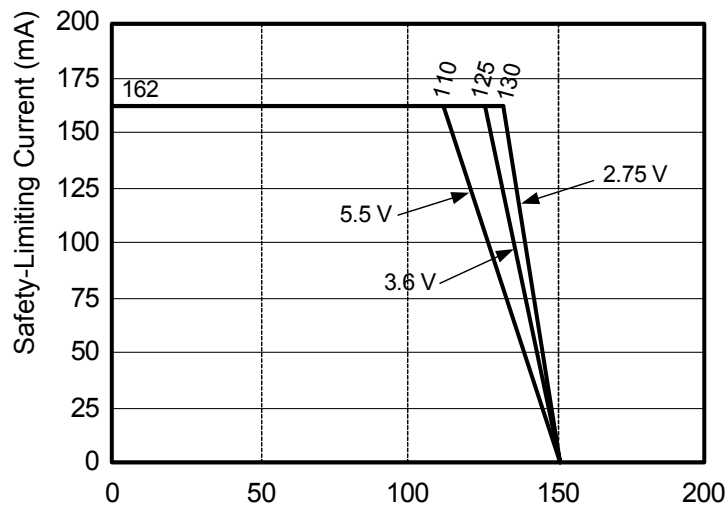
| Parameter                                                                                                                                                                                                                              | Symbol     | Test Condition                                                                                                                           | Characteristic | Unit     |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------|------------------------------------------------------------------------------------------------------------------------------------------|----------------|----------|
| Maximum Working Insulation Voltage                                                                                                                                                                                                     | $V_{IORM}$ |                                                                                                                                          | 560            | V peak   |
| Input to Output Test Voltage                                                                                                                                                                                                           | $V_{PR}$   | Method a<br>After Environmental Tests<br>Subgroup 1<br>( $V_{IORM} \times 1.6 = V_{PR}$ , $t_m = 60$ sec,<br>Partial Discharge $< 5$ pC) | 896            | V peak   |
|                                                                                                                                                                                                                                        |            | Method b1<br>( $V_{IORM} \times 1.875 = V_{PR}$ , 100%<br>Production Test, $t_m = 1$ sec,<br>Partial Discharge $< 5$ pC)                 | 1050           |          |
|                                                                                                                                                                                                                                        |            | After Input and/or Safety Test<br>Subgroup 2/3<br>( $V_{IORM} \times 1.2 = V_{PR}$ , $t_m = 60$ sec,<br>Partial Discharge $< 5$ pC)      | 672            |          |
| Highest Allowable Overvoltage (Transient Overvoltage, $t_{TR} = 10$ sec)                                                                                                                                                               | $V_{TR}$   |                                                                                                                                          | 4000           | V peak   |
| Pollution Degree (DIN VDE 0110, Table 1)                                                                                                                                                                                               |            |                                                                                                                                          | 2              |          |
| Insulation Resistance at $T_S$ , $V_{IO} = 500$ V                                                                                                                                                                                      | $R_S$      |                                                                                                                                          | $>10^9$        | $\Omega$ |
| <b>*Note:</b> This isolator is suitable for basic electrical isolation only within the safety limit data. Maintenance of the safety data is ensured by protective circuits. The Si84xx provides a climate classification of 40/125/21. |            |                                                                                                                                          |                |          |

Table 10. IEC Safety Limiting Values

| Parameter                                                                                                       | Symbol | Test Condition                                                                                      | Min | Typ | Max | Unit        |
|-----------------------------------------------------------------------------------------------------------------|--------|-----------------------------------------------------------------------------------------------------|-----|-----|-----|-------------|
| Case Temperature                                                                                                | $T_S$  |                                                                                                     | —   | —   | 150 | $^{\circ}C$ |
| Safety input, output, or supply current                                                                         | $I_S$  | $\theta_{JA} = 107^{\circ}C/W$ ,<br>$V_I = 5.5$ V,<br>$T_J = 150^{\circ}C$ ,<br>$T_A = 25^{\circ}C$ | —   | —   | 210 | mA          |
| <b>*Note:</b> Maximum value allowed in the event of a failure; also see the thermal derating curve in Figure 3. |        |                                                                                                     |     |     |     |             |

**Table 11. Thermal Characteristics**

| Parameter                                                                                                                                      | Symbol        | Test Condition                            | Min | Typ | Max | Unit |
|------------------------------------------------------------------------------------------------------------------------------------------------|---------------|-------------------------------------------|-----|-----|-----|------|
| IC Junction-to-Case Thermal Resistance                                                                                                         | $\theta_{JC}$ | Thermocouple located at center of package | —   | 45  | —   | °C/W |
| IC Junction-to-Air Thermal Resistance                                                                                                          | $\theta_{JA}$ |                                           | —   | 107 | —   | °C/W |
| Device Power Dissipation*                                                                                                                      | $P_D$         |                                           | —   | —   | 250 | mW   |
| *Note: The Si8430-C-IS is tested with $V_{DD1} = V_{DD2} = 5.5$ V, $T_J = 150$ °C, $C_L = 15$ pF, input a 150 Mbps 50% duty cycle square wave. |               |                                           |     |     |     |      |

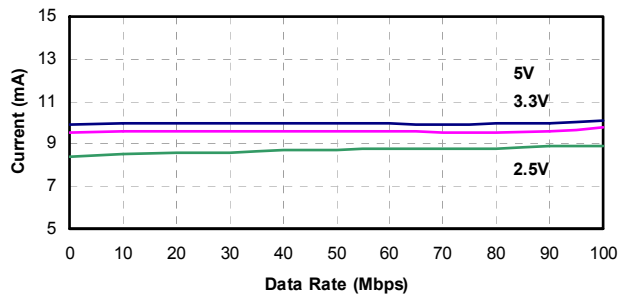


**Figure 3. Thermal Derating Curve, Dependence of Safety Limiting Values with Case Temperature per DIN EN 60747-5-2**

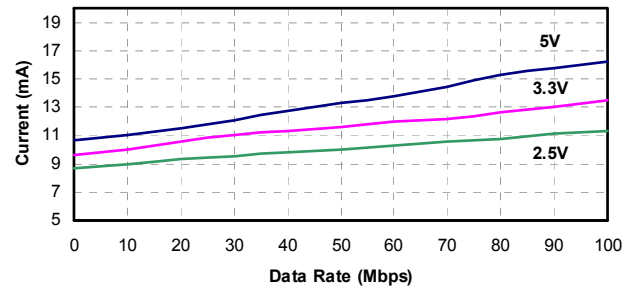


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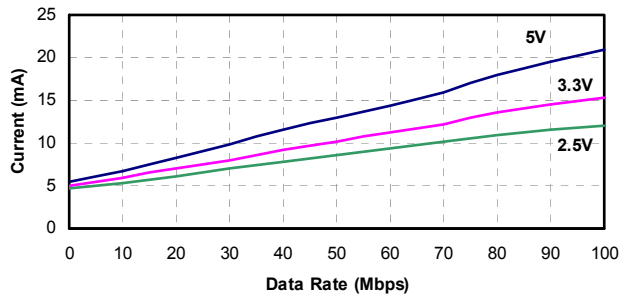
## 2. Typical Performance Characteristics



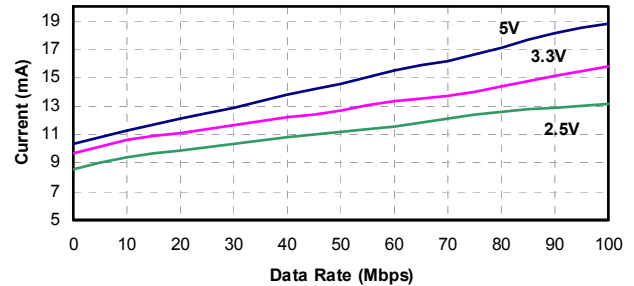
**Figure 4. Si8430/35 Typical  $V_{DD1}$  Supply Current vs. Data Rate 5, 3.3, and 2.5 V Operation**



**Figure 6. Si8431 Typical  $V_{DD1}$  Supply Current vs. Data Rate 5, 3.3, and 2.5 V Operation**

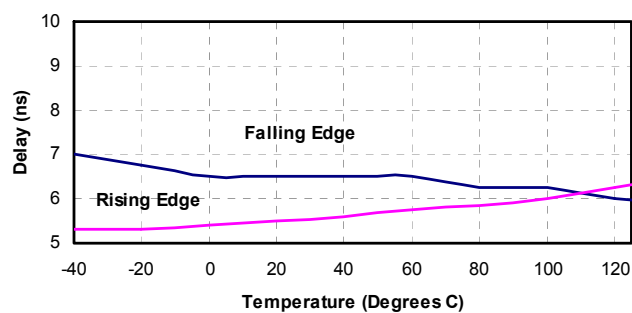


**Figure 5. Si8430/35 Typical  $V_{DD2}$  Supply Current vs. Data Rate 5, 3.3, and 2.5 V Operation (15 pF Load)**

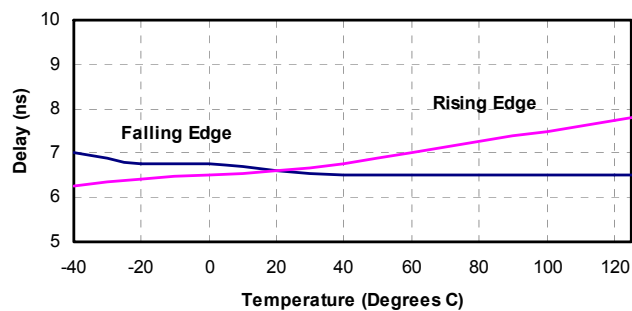


**Figure 7. Si8431 Typical  $V_{DD2}$  Supply Current vs. Data Rate 5, 3.3, and 2.5 V Operation (15 pF Load)**

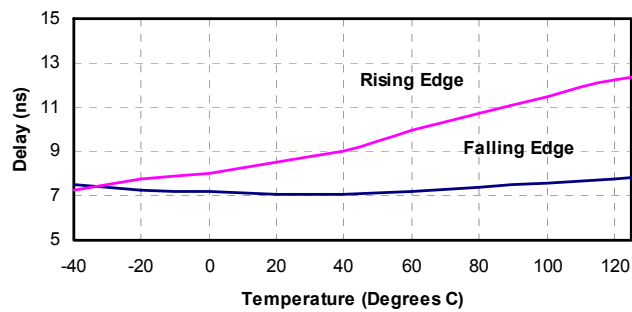
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**Figure 8. Propagation Delay  
vs. Temperature 5 V Operation**



**Figure 9. Propagation Delay  
vs. Temperature 3.3 V Operation**



**Figure 10. Propagation Delay  
vs. Temperature 2.5 V Operation**



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### 3. Application Information

#### 3.1. Theory of Operation

The operation of an Si8430 channel is analogous to that of an opto coupler, except an RF carrier is modulated instead of light. This simple architecture provides a robust isolated data path and requires no special considerations or initialization at start-up. A simplified block diagram for a single Si8430 channel is shown in Figure 11. A channel consists of an RF transmitter and receiver separated by a transformer.

Referring to the transmitter, input A modulates the carrier provided by an RF oscillator using on/off keying and applies the resulting waveform to the primary of the transformer. The receiver contains a demodulator that decodes the input state according to its RF energy content and applies the result to output B via the output driver.

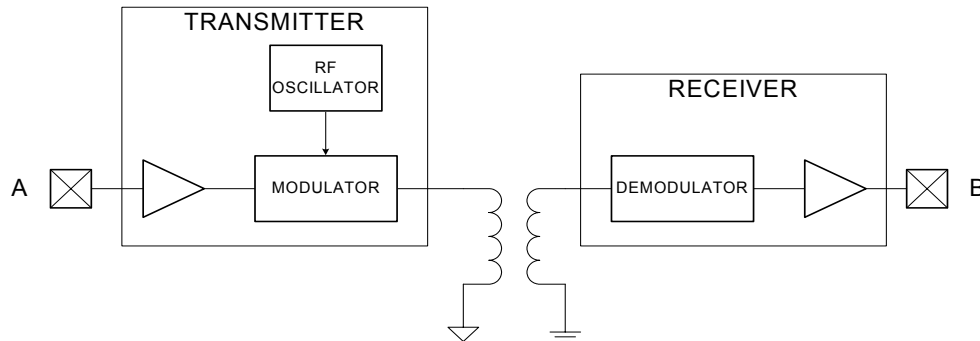


Figure 11. Simplified Channel Diagram

#### 3.2. Eye Diagram

Figure 12 illustrates an eye-diagram taken on an Si8430. The test used an Anritsu (MP1763C) Pulse Pattern Generator for the data source. The output of the generator's clock and data from an Si8430 were captured on an oscilloscope. The results illustrate that data integrity was maintained even at the high data rate of 150 Mbps. The results also show that very low pulse width distortion and very little jitter were exhibited.

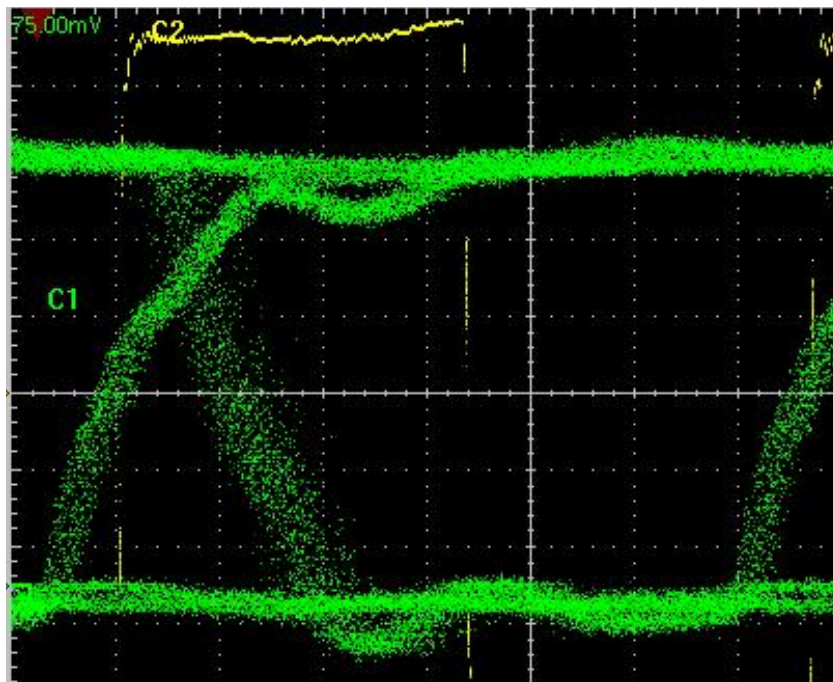


Figure 12. Eye Diagram

## 4. Layout Recommendations

Dielectric isolation is a set of specifications produced by the safety regulatory agencies from around the world that describes the physical construction of electrical equipment that derives power from a high-voltage power system such as 100–240 V<sub>AC</sub> systems or industrial power systems. The dielectric test (or HIPOT test) given in the safety specifications places a very high voltage between the input power pins of a product and the user circuits and the user touchable surfaces of the product. For the IEC relating to products deriving their power from the 220–240 V power grids, the test voltage is 2500 V<sub>AC</sub> (or 3750 V<sub>DC</sub>—the peak equivalent voltage).

There are two terms described in the safety specifications:

- Creepage—the distance along the insulating surface an arc may travel.
- Clearance—the distance through the shortest path through air that an arc may travel.

Figure 13 illustrates the accepted method of providing the proper creepage distance along the surface. For a 220–240 V application, this distance is 8 mm and the wide body SOIC package must be used. There must be no copper traces within this 8 mm exclusion area, and the surface should have a conformal coating such as solder resist. The digital isolator chip must straddle this exclusion area.

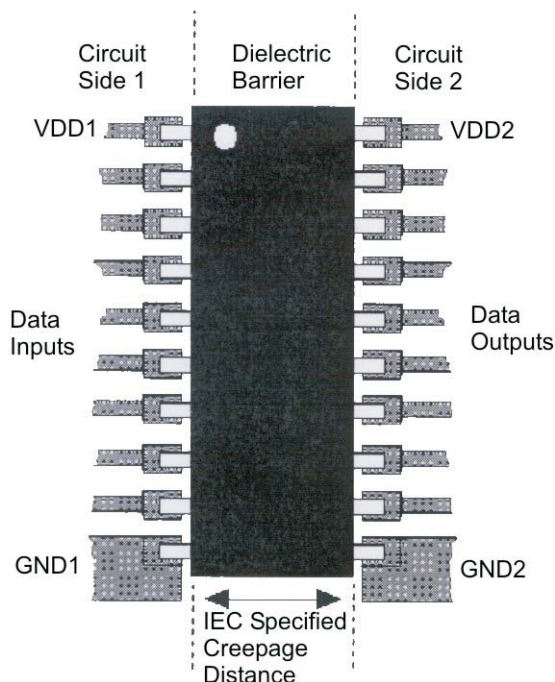


Figure 13. Creepage Distance

### 4.1. Supply Bypass

The Si843x requires a 0.1  $\mu$ F bypass capacitor between V<sub>DD1</sub> and GND1 and V<sub>DD2</sub> and GND2. The capacitor should be placed as close as possible to the package.

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## 4.2. Input and Output Characteristics

The Si843x inputs and outputs are standard CMOS drivers/receivers. The Si844x inputs and outputs are standard CMOS drivers/receivers. Table 12 details powered and unpowered operation of the Si84xx.

**Table 12. Si84xx Operation Table**

| $V_I$<br>Input <sup>1,2</sup> | EN<br>Input <sup>1,2,3,4</sup> | VDDI<br>State <sup>1,5,6</sup> | VDDO<br>State <sup>1,5,6</sup> | $V_O$<br>Output <sup>1,2</sup> | Comments                                                                                                                                                      |
|-------------------------------|--------------------------------|--------------------------------|--------------------------------|--------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------|
| H                             | H or NC                        | P                              | P                              | H                              | Enabled, normal operation.                                                                                                                                    |
| L                             | H or NC                        | P                              | P                              | L                              |                                                                                                                                                               |
| X                             | L                              | P                              | P                              | Hi-Z                           | Disabled                                                                                                                                                      |
| X                             | H or NC                        | UP                             | P                              | L                              | Upon the transition of VDDI from unpowered to powered, $V_O$ returns to the same state as $V_I$ in less than 1 $\mu$ s.                                       |
| X                             | L                              | UP                             | P                              | Hi-Z                           | Disabled                                                                                                                                                      |
| X                             | X                              | P                              | UP                             | L                              | Upon the transition of VDDI from unpowered to powered, $V_O$ returns to the same state as $V_I$ in less than 1 $\mu$ s, if EN is in either the H or NC state. |

**Notes:**

1. VDDI and VDDO are the input and output power supplies.  $V_I$  and  $V_O$  are the respective input and output terminals. EN is the enable control input located on the same output side.
2. X = not applicable; H = Logic High; L = Logic Low; Hi-Z = High Impedance.
3. It is recommended that the enable inputs be connected to an external logic high or low level when the Si84xx is operating in noisy environments.
4. No Connect (NC) replaces EN1 on Si8430/35. No Connect replaces EN2 on the Si8435. No Connects are not internally connected and can be left floating, tied to VDD, or tied to GND.
5. "Powered" state (P) is defined as  $2.375\text{ V} < \text{VDD} < 5.5\text{ V}$ .
6. "Unpowered" state (UP) is defined as  $\text{VDD} = 0\text{ V}$ .

## 4.3. Enable (EN1, EN2) Inputs

Enable inputs EN1 and EN2 can be used for multiplexing, for clock sync, or other output control. EN1, EN2 logic operation is summarized for each isolator product in Table 13. These inputs are internally pulled-up to local VDD by a 9  $\mu$ A current source allowing them to be connected to an external logic level (high or low) or left floating. To minimize noise coupling, do **not** connect circuit traces to EN1 or EN2 if they are left floating. If EN1, EN2 are unused, it is recommended they be connected to an external logic level, especially if the Si84xx is operating in a noisy environment.

**Table 13. Enable Input Truth Table**

| P/N                                                       | EN1* | EN2* | Operation                                                    |
|-----------------------------------------------------------|------|------|--------------------------------------------------------------|
| Si8430                                                    | —    | H    | Outputs B1, B2, B3 are enabled.                              |
|                                                           | —    | L    | Outputs B1, B2, B3 are disabled and in high impedance state. |
| Si8431                                                    | H    | X    | Output A3 enabled.                                           |
|                                                           | L    | X    | Output A3 disabled and in high impedance state.              |
|                                                           | X    | H    | Outputs B1, B2 are enabled.                                  |
|                                                           | X    | L    | Outputs B1, B2 are disabled and in high impedance state.     |
| Si8435                                                    | —    | —    | Outputs B1, B2, B3 are enabled.                              |
| *Note: X = not applicable; H = Logic High; L = Logic Low. |      |      |                                                              |

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#### 4.4. RF Radiated Emissions

The Si8430 family uses a RF carrier frequency of approximately 2.1 GHz. This will result in a small amount of radiated emissions at this frequency and its harmonics. The radiation is not from the IC chip but due to a small amount of RF energy driving the isolated ground planes which can act as a dipole antenna.

The unshielded Si8430 evaluation board passes FCC requirements. Table 14 shows measured emissions compared to FCC requirements.

Radiated emissions can be reduced if the circuit board is enclosed in a shielded enclosure or if the PCB is a less efficient antenna.

**Table 14. Radiated Emissions**

| Frequency<br>(GHz) | Measured<br>(dB $\mu$ V/m) | FCC Spec<br>(dB $\mu$ V/m) | Compared<br>to Spec<br>(dB) |
|--------------------|----------------------------|----------------------------|-----------------------------|
| 2.094              | 70.0                       | 74.0                       | −4.0                        |
| 2.168              | 68.3                       | 74.0                       | −5.7                        |
| 4.210              | 61.9                       | 74.0                       | −12.1                       |
| 4.337              | 60.7                       | 74.0                       | −13.3                       |
| 6.315              | 58.3                       | 74.0                       | −15.7                       |
| 6.505              | 60.7                       | 74.0                       | −13.3                       |
| 8.672              | 45.6                       | 74.0                       | −28.4                       |

## 4.5. RF Immunity and Common Mode Transient Immunity

The Si8430 family has very high common mode transient immunity while transmitting data. This is typically measured by applying a square pulse with very fast rise/fall times between the isolated grounds. Measurements show no failures up to 30 kV/ $\mu$ s. During a high surge event the output may glitch low for up to 20–30 ns, but the output corrects immediately after the surge event.

The Si843x family passes the industrial requirements of CISPR24 for RF immunity of 3 V/m using an unshielded evaluation board. As shown in Figure 14, the isolated ground planes form a parasitic dipole antenna, while Figure 15 shows the RMS common mode voltage versus frequency above which the Si843x becomes susceptible to data corruption. To avoid compromising data, care must be taken to keep RF common-mode voltage below the envelope specified in Figure 15. The PCB should be laid-out to not act as an efficient antenna for the RF frequency of interest. RF susceptibility is also significantly reduced when the end system is housed in a metal enclosure, or otherwise shielded.

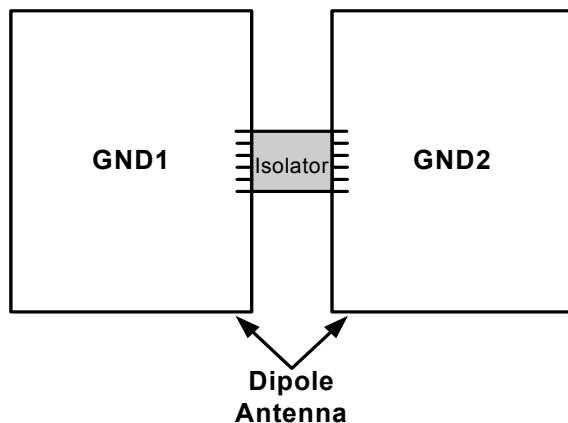


Figure 14. Dipole Antenna

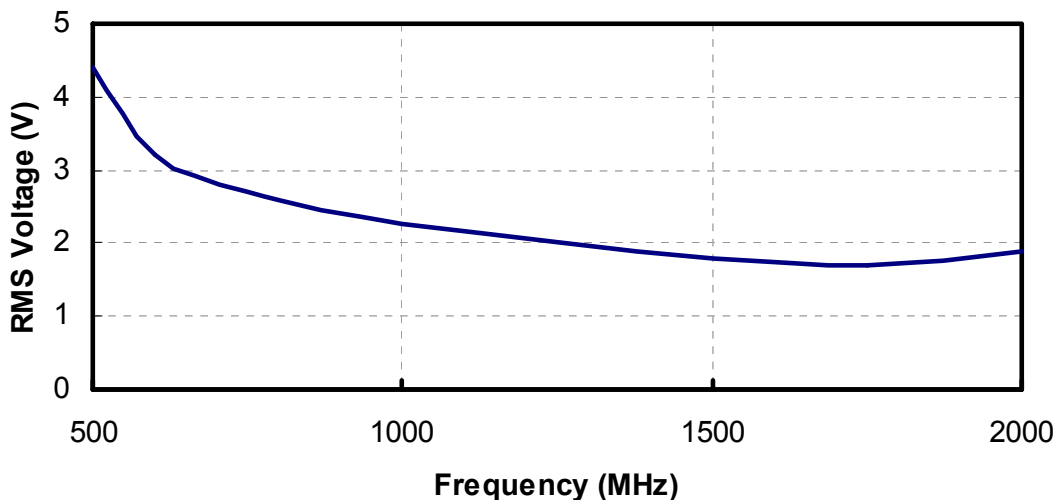
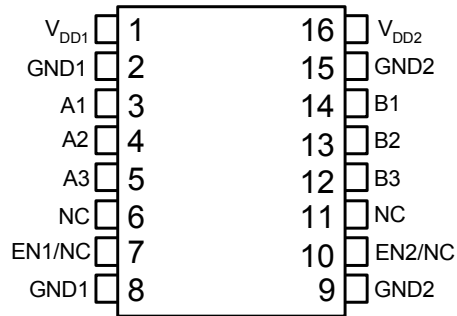


Figure 15. RMS Common Mode Voltage vs. Frequency



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## 5. Pin Descriptions



Top View

### Wide Body SOIC

| Name             | SOIC-16 Pin# | Type           | Description                                |
|------------------|--------------|----------------|--------------------------------------------|
| V <sub>DD1</sub> | 1            | Supply         | Side 1 power supply.                       |
| GND1             | 2            | Ground         | Side 1 ground.                             |
| A1               | 3            | Digital Input  | Side 1 digital input.                      |
| A2               | 4            | Digital Input  | Side 1 digital input.                      |
| A3               | 5            | Digital I/O    | Side 1 digital input or output.            |
| NC               | 6            | NA             | No Connect.                                |
| EN1/NC*          | 7            | Digital Input  | Side 1 active high enable. NC on Si8430/35 |
| GND1             | 8            | Ground         | Side 1 ground.                             |
| GND2             | 9            | Ground         | Side 2 ground.                             |
| EN2/NC*          | 10           | Digital Input  | Side 2 active high enable. NC on Si8435.   |
| NC               | 11           | NA             | No Connect.                                |
| B3               | 12           | Digital I/O    | Side 2 digital input or output.            |
| B2               | 13           | Digital Output | Side 2 digital output.                     |
| B1               | 14           | Digital Output | Side 2 digital output.                     |
| GND2             | 15           | Ground         | Side 2 ground.                             |
| V <sub>DD2</sub> | 16           | Supply         | Side 2 power supply.                       |

**\*Note:** No Connect. These pins are not internally connected. They can be left floating, tied to VDD or tied to GND.

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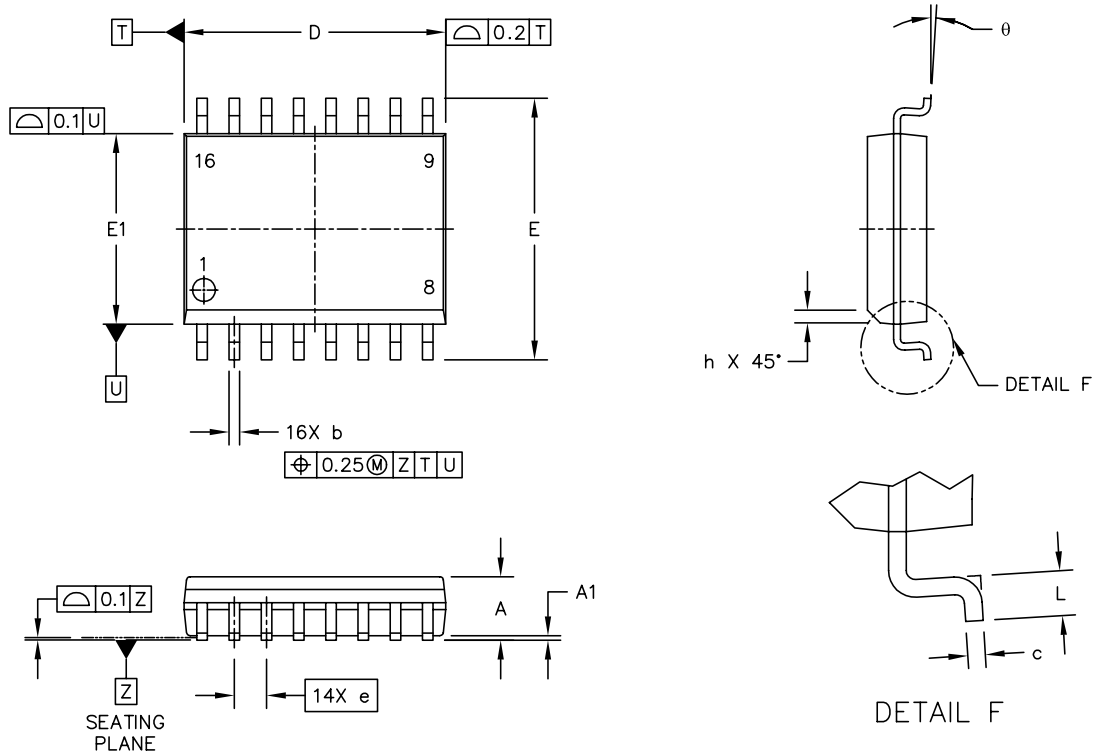
## 6. Ordering Guide

| Ordering Part Number                                                                                                                                                                                                       | Number of Inputs<br>V <sub>DD1</sub> Side | Number of Inputs<br>V <sub>DD2</sub> Side | Maximum<br>Data Rate | Temperature   | Package<br>Type |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------|-------------------------------------------|----------------------|---------------|-----------------|
| Si8430-A-IS                                                                                                                                                                                                                | 3                                         | 0                                         | 1                    | –40 to 125 °C | SOIC-16         |
| Si8430-B-IS                                                                                                                                                                                                                | 3                                         | 0                                         | 10                   | –40 to 125 °C | SOIC-16         |
| Si8430-C-IS                                                                                                                                                                                                                | 3                                         | 0                                         | 150                  | –40 to 125 °C | SOIC-16         |
| Si8431-A-IS                                                                                                                                                                                                                | 2                                         | 1                                         | 1                    | –40 to 125 °C | SOIC-16         |
| Si8431-B-IS                                                                                                                                                                                                                | 2                                         | 1                                         | 10                   | –40 to 125 °C | SOIC-16         |
| Si8431-C-IS                                                                                                                                                                                                                | 2                                         | 1                                         | 150                  | –40 to 125 °C | SOIC-16         |
| Si8435-B-IS                                                                                                                                                                                                                | 3                                         | 0                                         | 10                   | –40 to 125 °C | SOIC-16         |
| <b>Note:</b> All packages are Pb-free and RoHS Compliant. Moisture sensitivity level is MSL2 with peak reflow temperature of 260 °C according to the JEDEC industry standard classifications, and peak solder temperature. |                                           |                                           |                      |               |                 |

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## 7. Package Outline: Wide Body SOIC

Figure 16 illustrates the package details for the Quad-Channel Digital Isolator. Table 14 lists the values for the dimensions shown in the illustration.



**Figure 16. 16-Pin Wide Body SOIC**

**Table 14. Package Diagram Dimensions**

| Symbol | Millimeters |      |
|--------|-------------|------|
|        | Min         | Max  |
| A      | —           | 2.65 |
| A1     | 0.1         | 0.3  |
| D      | 10.3 BSC    |      |
| E      | 10.3 BSC    |      |
| E1     | 7.5 BSC     |      |
| b      | 0.31        | 0.51 |
| c      | 0.20        | 0.33 |
| e      | 1.27 BSC    |      |
| h      | 0.25        | 0.75 |
| L      | 0.4         | 1.27 |
| θ      | 0°          | 7°   |

## DOCUMENT CHANGE LIST

### Revision 0.1 to Revision 0.11

- Updated Table 7, “Regulatory Information,” on page 14.
- Minor typographical edits.

### Revision 0.11 to Revision 0.2

- Updated Supply Current specifications in Table 1, “Electrical Characteristics,” on page 4, Table 2, “Electrical Characteristics,” on page 7, and Table 3, “Electrical Characteristics,” on page 10.
- Updated performance plots in Figures 4, 5, 6, and 7.
- Added NC note (Note 3) to Table 10, “Si84xx Truth Table (Positive Logic),” on page 16.
- Added NC note (\*) to “5. Pin Descriptions” on page 25.

### Revision 0.2 to Revision 0.3

- Updated Notes to Tables 1, 2, & 3.
- Updated Figure 2.
- Updated Tables 6–11 to clarify specifications, test limits, & device characteristics.

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**NOTES:**

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